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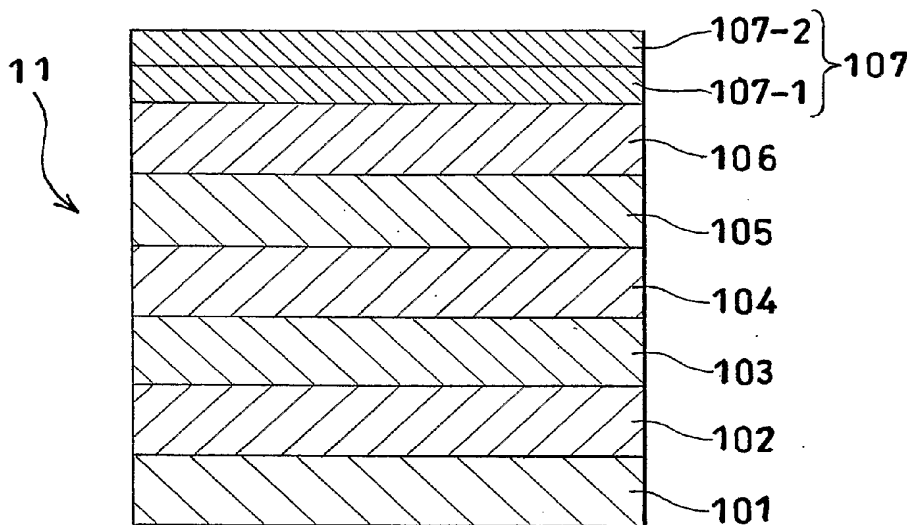
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(54) Title: GALLIUM NITRIDE-BASED SEMICONDUCTOR DEVICE



(57) Abstract: A gallium nitride-based semiconductor device has a p-type layer that is a gallium nitride (GaN) compound semiconductor layer containing a p-type impurity and exhibiting p-type conduction. The p-type layer includes a top portion and an inner portion located under the top portion. The inner portion contains the p-type impurity and, in combination therewith, hydrogen. The top portion includes a region containing a Group III element and a Group V element at a non-stoichiometric atomic ratio.

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